



30V N-Channel Trench Power MOSFET

General Description

The SJF30N042 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a wide variety of applications.

Features

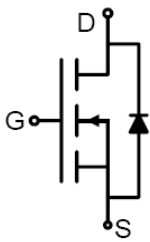
- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handling capability
- Lead free product is acquired

Application

- Load switch
- PWM applications
- Power management

Key Performance Parameters

Parameter	Value	Unit
V_{DS}	30	V
$R_{DS(ON_TYP)}$	4.3	m Ω
I_D	99	A
Q_G	25	nC



Schematic Diagram



TO-220 top view



Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJF30N042	SJF30N042	TO-220	Tube	\	\	1000 Pcs

Table 1. Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	30	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 20	V
I_D	Drain Current-Continuous($T_c=25^\circ\text{C}$)	99	A
	Drain Current-Continuous($T_c=100^\circ\text{C}$)	62	A
I_{DM} (pulse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	396	A
P_D	Maximum Power Dissipation($T_c=25^\circ\text{C}$)	83	W
	Maximum Power Dissipation($T_c=100^\circ\text{C}$)	33	W
E_{AS}	Avalanche energy (Note 2)	132	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		1.5	$^\circ\text{C/W}$



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Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =25℃			1	μA
		V _{DS} =30V, V _{GS} =0V T _J =125℃			100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1		2.5	V
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		32		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =15A T _J =25℃		4.3	5.4	mΩ
		V _{GS} =4.5V, I _D =10A T _J =25℃		6.2	8.1	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz		1730		pF
C _{oss}	Output Capacitance			192		pF
C _{rss}	Reverse Transfer Capacitance			171		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		1.1		Ω
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =10V, V _{DS} =15V, R _L =1Ω, R _{GEN} =3Ω		11		nS
t _r	Turn-on Rise Time			55		nS
t _{d(off)}	Turn-Off Delay Time			198		nS
t _f	Turn-Off Fall Time			120		nS
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =15A		25		nC
Q _{gs}	Gate-Source Charge			5		nC
Q _{gd}	Gate-Drain Charge			10		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				99	A
V _{SD}	Forward on Voltage (Note 3)	V _{GS} =0V, I _S =20A			1.2	V
t _{rr}	Reverse Recovery Time	I _F =20A, dI/dt=100A/μs		12		ns
Q _{rr}	Reverse Recovery Charge	I _F =20A, dI/dt=100A/μs		4		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

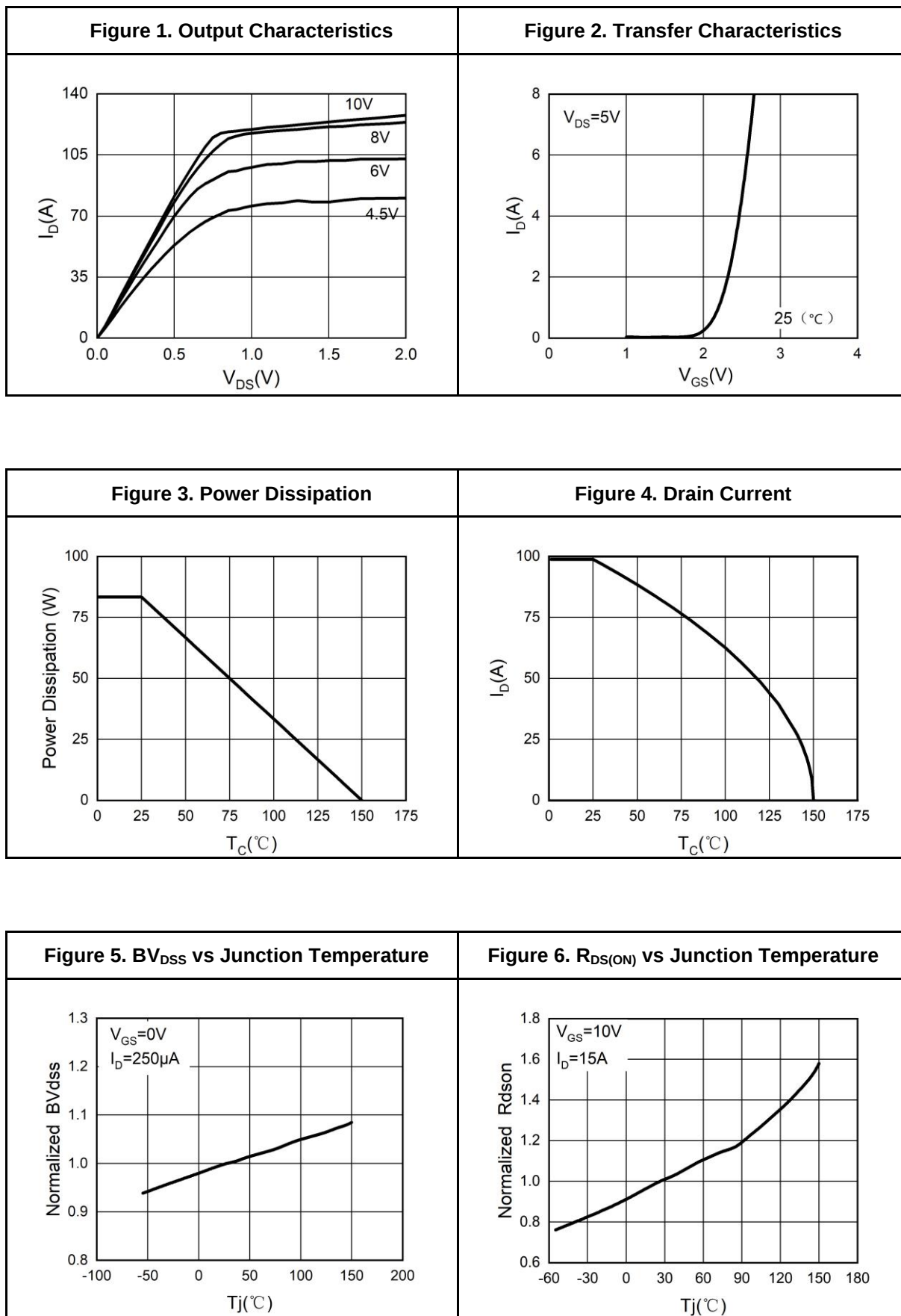
Notes 2.EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=20V, V_G=10V, R_g=25\Omega, L=0.5\text{mH}$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



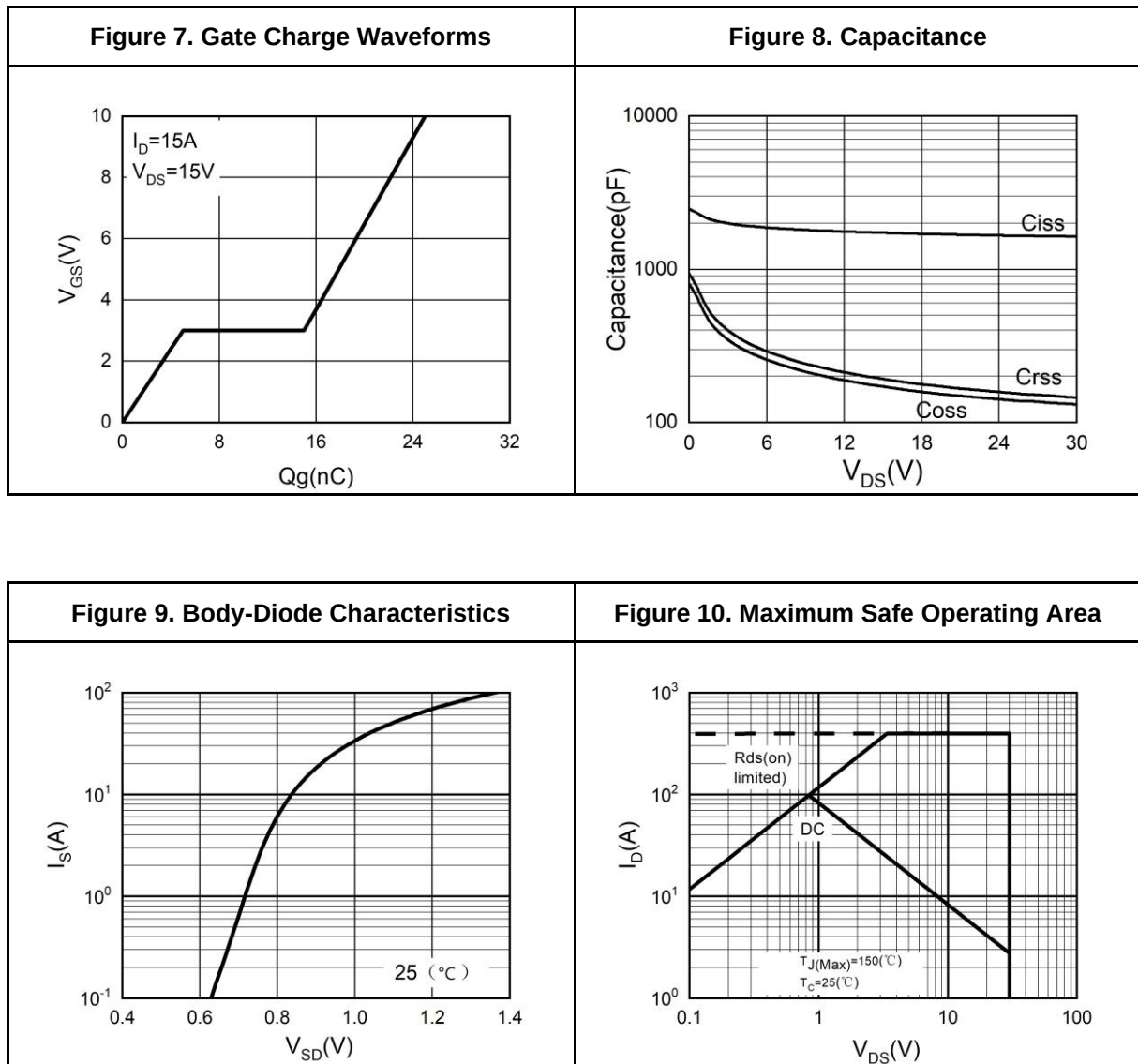
30V N-Channel Trench Power MOSFET

Typical Electrical And Thermal Characteristics (Curves)



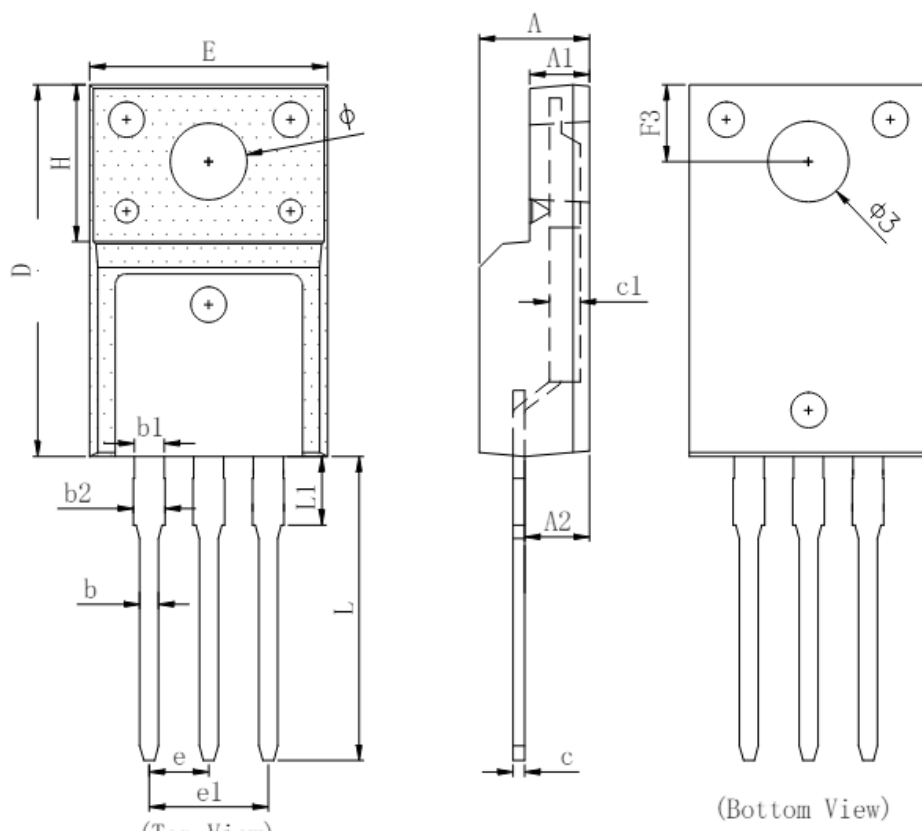


Typical Electrical And Thermal Characteristics (Curves)





TO-220F Package Information



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	4.500	4.700	4.900
A1	2.340	2.540	2.740
A2	2.560	2.760	2.960
b	0.700	0.800	0.950
b1	1.180	1.280	1.430
b2	1.250	1.350	1.550
c	0.400	0.500	0.650
c1	1.200	1.300	1.350
D	15.570	15.870	16.170
H	6.700 REF		
E	9.960	10.160	10.360
e	2.540 BSC		
e1	5.080 BSC		
L	12.680	12.980	13.280
L1	2.780	2.930	3.080
F3	3.150	3.300	3.450
ϕ	3.030	3.180	3.450
$\phi 3$	3.150	3.450	3.650

(注：全尺寸测量时c1不测)



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